FTK30N15P

150V N-Channel MOSFETs

General Description

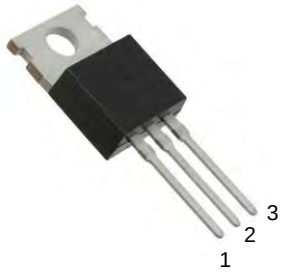
These N-Channel enhancement mode power field effect transistors are using trench DMOS technology. This advanced technology has been especially tailored to minimize on-state resistance, provide superior switching performance, and withstand high energy pulse in the avalanche and commutation mode. These devices are well suited for high efficiency fast switching applications.

BVDSS	RDSON	ID
150V	65mΩ	28A

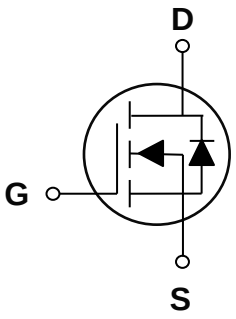
Features

- *150V,28A, RDS(ON) 65mΩ@VGS = 10V*
- *VGS Guarantee ±25V*
- *Improved dv/dt capability*
- *Fast switching*
- *Green Device Available*

TO-220 Pin Configuration



1. Gate
2. Drain
3. Source



Applications

- *Notebook*
- *Load Switch*
- *LED applications*
- *Li battery pack application*

Absolute Maximum Ratings (Tc=25℃ unless otherwise noted)

Symbol	Parameter	Rating	Units
V_{DS}	Drain-Source Voltage	150	V
V_{GS}	Gate-Source Voltage	±25	V
I_D	Drain Current – Continuous (T_C=25℃)	28	A
	Drain Current – Continuous (T_C=100℃)	17.7	A
I_{DM}	Drain Current – Pulsed[1]	112	A
EAS	Single Pulse Avalanche Energy[4]	242	mJ
IAS	Single Pulse Avalanche Current[4]	22	A
P_D	Power Dissipation (T_C=25℃)	113	W
	Power Dissipation – Derate above 25℃	0.91	W/℃
T_{STG}	Storage Temperature Range	-55 to 150	℃
T_J	Operating Junction Temperature Range	-55 to 150	℃

Thermal Characteristics

Symbol	Parameter	Typ.	Max.	Unit
$R_{\theta JA}$	Thermal Resistance Junction to ambient	---	62	℃/W
$R_{\theta JC}$	Thermal Resistance Junction to Case	---	1.1	℃/W

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Electrical Characteristics (T_J=25℃, unless otherwise noted)

Off Characteristics

Symbol	Parameter	Conditions	Min.	Typ.	Max.	Unit
BV_{DSS}	Drain-Source Breakdown Voltage	V_{GS}=0V , I_D=250uA	150	---	---	V
$\triangle BV_{DSS}/\triangle T_J$	BV_{DSS} Temperature Coefficient	Reference to 25℃ , I_D=1mA	---	0.08	---	V/℃
I_{DSS}	Drain-Source Leakage Current	V_{DS}=150V , V_{GS}=0V , T_J=25℃	---	---	1	uA
		V_{DS}=120V , V_{GS}=0V , T_J=125℃	---	---	30	uA
I_{GSS}	Gate-Source Leakage Current	V_{GS}=±25V , V_{DS}=0V	---	---	±100	nA

On Characteristics

$R_{DS(ON)}$	Static Drain-Source On-Resistance	V_{GS}=10V , I_D=15A	---	52	65	mΩ
$V_{GS(th)}$	Gate Threshold Voltage	V_{GS}=V_{DS} , I_D =250uA	2	3	4	V
$\triangle V_{GS(th)}$	$V_{GS(th)}$ Temperature Coefficient		---	-2.5	---	mV/℃

Dynamic and switching Characteristics

Q_g	Total Gate Charge[2,3]	V_{DS}=75V , V_{GS}=10V , I_D=4A	---	30	45	nC
Q_{gs}	Gate-Source Charge[2,3]		---	8.7	14	
Q_{gd}	Gate-Drain Charge[2,3]		---	8	15	
$T_{d(on)}$	Turn-On Delay Time[2,3]	V_{DD}=30V , V_{GS}=10V , R_G=6Ω I_D=1A	---	14.5	28	ns
T_r	Rise Time[2,3]		---	19.2	18	
$T_{d(off)}$	Turn-Off Delay Time[2,3]		---	33.6	60	
T_f	Fall Time[2,3]		---	22.8	25	
C_{iss}	Input Capacitance	V_{DS}=30V , V_{GS}=0V , F=1MHz	---	1790	3000	pF
C_{oss}	Output Capacitance		---	160	300	
C_{rss}	Reverse Transfer Capacitance		---	82	160	
R_g	Gate Resistance	V_{GS}=0V , V_{DS}=0V , F-1MHz		1.4	2.8	Ω

Drain-Source Diode Characteristics and Maximum Ratings

Symbol	Parameter	Conditions	Min.	Typ.	Max.	Unit
I_S	Continuous Source Current	V_G=V_D=0V , Force Current	---	---	28	A
I_{SM}	Pulsed Source Current		---	---	56	A
V_{SD}	Diode Forward Voltage	V_{GS}=0V , I_S=1A , T_J=25℃	---	---	1.2	V
t_{rr}	Reverse Recovery Time[2]	V_{GS}=0V,I_S=1A , dI/dt=100A/μs T_J=25℃	---	---	---	ns
Q_{rr}	Reverse Recovery Charge[2]		---	---	---	nC

Note :
1. Repetitive Rating : Pulsed width limited by maximum junction temperature.
2. The data tested by pulsed , pulse width ≦ 300us , duty cycle ≦ 2%.
3. Essentially independent of operating temperature.
4. V_{DD}=50V,V_{GS}=10V,L=1mH,I_{AS}=22A.,R_G=25Ω ,Starting T_J=25℃.

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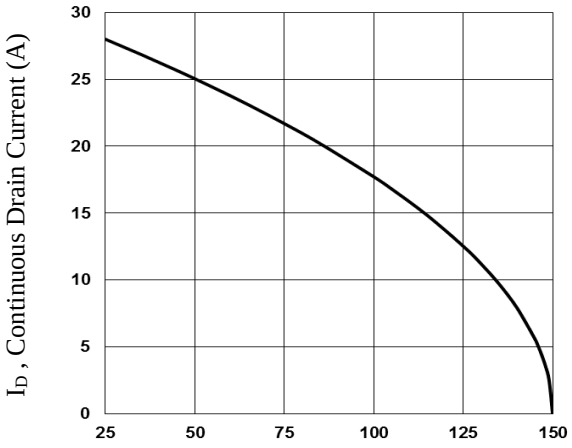


Fig.1 Continuous Drain Current vs. T_C

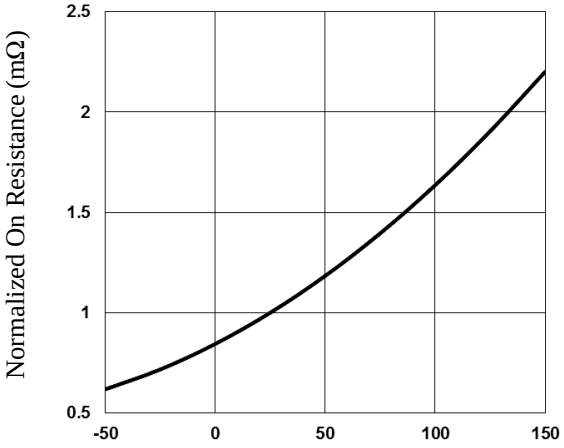


Fig.2 Normalized RDSON vs. T_J

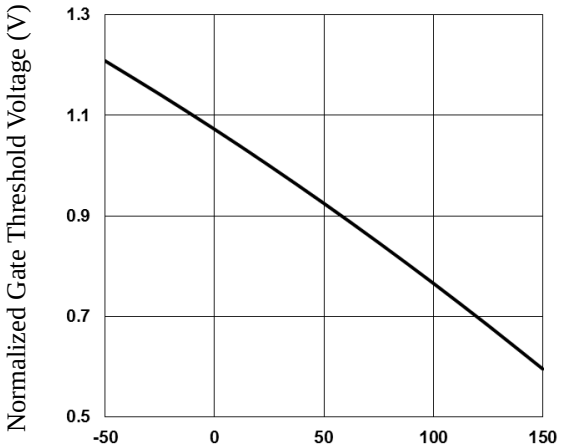


Fig.3 Normalized Vth vs. T_J

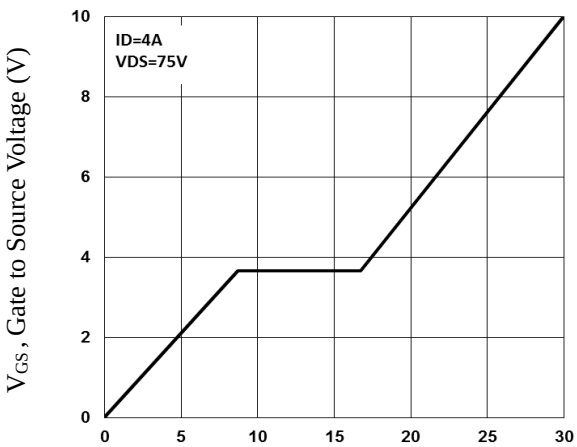


Fig.4 Gate Charge Characteristics

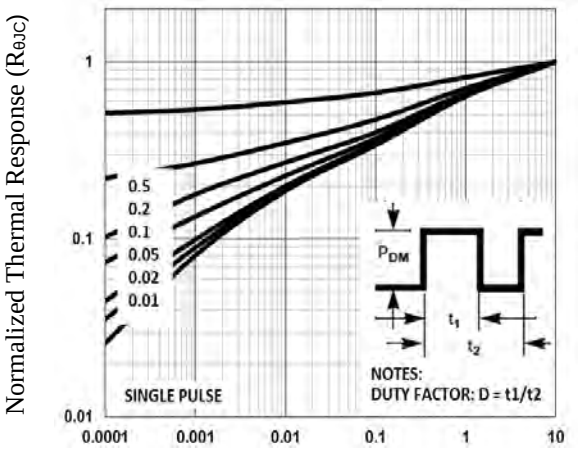


Fig.5 Normalized Transient Impedance

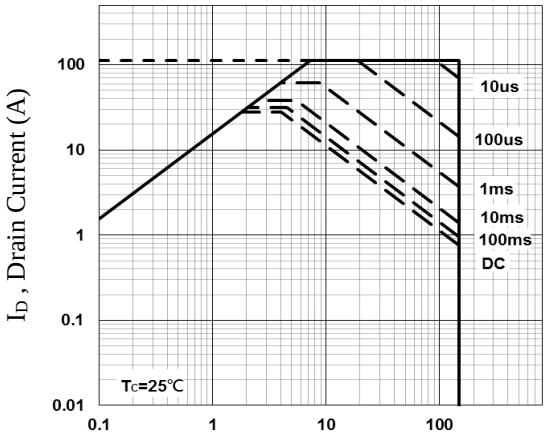


Fig.6 Maximum Safe Operation Area

150V N-Channel MOSFETs

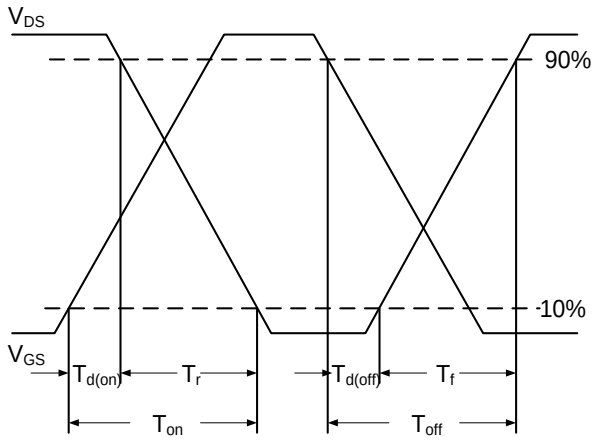


Fig.7 Switching Time Waveform

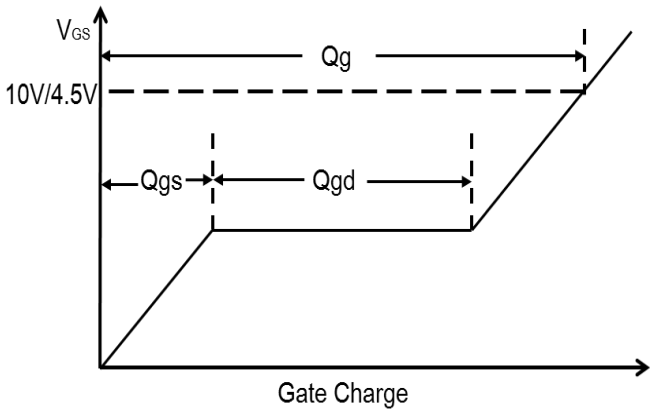
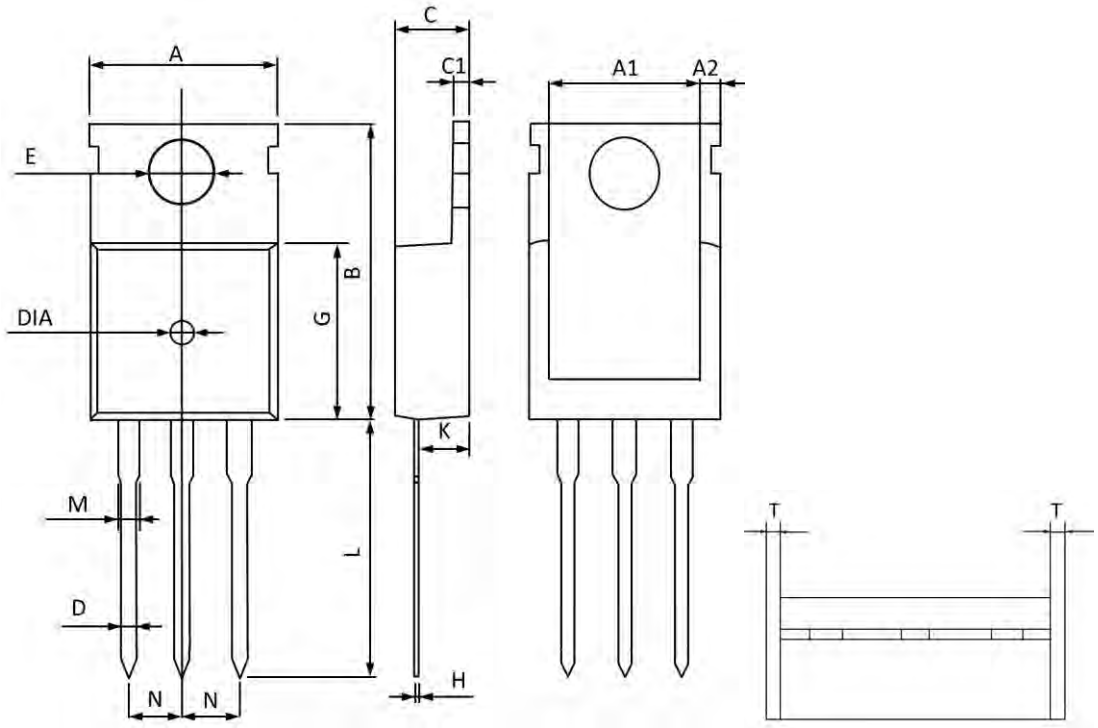


Fig.8 Gate Charge Waveform

150V N-Channel MOSFETs

TO-220 PACKAGE INFORMATION



Symbol	Dimensions In Millimeters		Dimensions In Inches	
	Min	Max	Min	Max
A	9.70	10.30	0.382	0.405
A1	8.44	8.84	0.333	0.348
A2	1.05	1.25	0.042	0.049
B	15.40	16.20	0.607	0.637
C	4.28	4.68	0.169	0.184
C1	1.10	1.50	0.044	0.059
D	0.60	1.00	0.024	0.039
E	3.40	3.80	0.134	0.149
G	8.70	9.30	0.343	0.366
H	0.40	0.60	0.016	0.023
K	2.10	2.70	0.083	0.106
L	12.80	13.60	0.504	0.535
L1	2.70	3.30	0.107	0.129
M	1.10	1.50	0.044	0.059
N	2.49	2.59	0.099	0.101
T	0.345	0.355	0.014	0.014
DIA	1.45	1.55	0.058	0.061